

# Molding Type Module IGBT, 1-in-1 Package, 1200 V and 400 A



**Dual INT-A-PAK** 

PRIMARY CHARACTERISTICS					
V <sub>CES</sub>	1200 V				
I <sub>C</sub> at T <sub>C</sub> = 80 °C	400 A				
$V_{CE(on)}$ (typical) at $I_C = 400$ A, 25 °C	1.90 V				
Speed	8 kHz to 30 kHz				
Package	Dual INT-A-PAK				
Circuit configuration	Single switch with AP diode				

#### **FEATURES**

- High short circuit capability, self limiting to 6 x I<sub>C</sub>
- 10 µs short circuit capability
- V<sub>CE(on)</sub> with positive temperature coefficient
- Low inductance case
- · Fast and soft reverse recovery antiparallel FWD
- Isolated copper baseplate using DCB (Direct Copper Bonding) technology
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATINS**

- Switching mode power supplies
- · AC inverter drives
- Electronic welders at f<sub>sw</sub> up to 20 kHz

#### **DESCRIPTION**

Vishay's IGBT power module provides ultralow conduction loss as well as short circuit ruggedness. It is designed for applications such as inverters and UPS.

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Collector to emitter voltage	V <sub>CES</sub>		1200	V	
Gate to emitter voltage	V <sub>GES</sub>		± 20	V	
Collector current at T <sub>.I</sub> = 150 °C		T <sub>C</sub> = 25 °C	650		
Collector current at 1 <sub>J</sub> = 150 °C	Ic	T <sub>C</sub> = 80 °C	400		
Pulsed collector current	I <sub>CM</sub> <sup>(1)</sup>	T <sub>C</sub> = 80 °C	800	Α	
Diode continuous forward current	IF		400		
Diode maximum forward current	I <sub>FM</sub>		800		
Maximum power dissipation	P <sub>D</sub>	T <sub>J</sub> = 150 °C	2500	W	
Short circuit withstand time	t <sub>SC</sub>	T <sub>J</sub> = 125 °C	10	μs	
l <sup>2</sup> t-value, diode	l <sup>2</sup> t	$V_R = 0 \text{ V}, \text{ t} = 10 \text{ ms}, \text{ T}_J = 125 ^{\circ}\text{C}$	27 500	A <sup>2</sup> s	
RMS isolation voltage	V <sub>ISOL</sub>	f = 50 Hz, t = 1 min	2500	V	

#### Note

<sup>(1)</sup> Repetitive rating: pulse width limited by maximum junction temperature

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IGBT ELECTRICAL SPECIFICATIONS (T <sub>C</sub> = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V <sub>(BR)CES</sub>	T <sub>J</sub> = 25 °C	1200	-	-	
Collector to emitter saturation voltage	V	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 400 A, T <sub>J</sub> = 25 °C	-	1.9	-	V
Collector to enfitter saturation voltage	V <sub>CE(on)</sub>	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 400 A, T <sub>J</sub> = 125 °C	-	2.1	-	]
Gate to emitter threshold voltage	V <sub>GE(th)</sub>	$V_{CE} = V_{GE}$ , $I_C = 8$ mA, $T_J = 25$ °C	5.0	6.2	7.0	
Zero gate voltage collector current	I <sub>CES</sub>	$V_{CE} = V_{CES}$ , $V_{GE} = 0$ V, $T_{J} = 25$ °C	-	-	5.0	mA
Gate to emitter leakage current	I <sub>GES</sub>	$V_{GE} = V_{GES}$ , $V_{CE} = 0$ V, $T_{J} = 25$ °C	-	-	400	nA



SWITCHING CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-on delay time	t <sub>d(on)</sub>		-	100	-	
Rise time	t <sub>r</sub>		-	60	-	ns
Turn-off delay time	t <sub>d(off)</sub>	$V_{CC} = 600 \text{ V}, I_{C} = 400 \text{ A}, R_{g} = 4 \Omega,$	-	420	-	
Fall time	t <sub>f</sub>	$V_{GE} = \pm 15 \text{ V}, T_{J} = 25 \text{ °C}$	-	60	-	
Turn-on switching loss	E <sub>on</sub>		-	33	-	- mJ
Turn-off switching loss	E <sub>off</sub>		-	42	-	
Turn-on delay time	t <sub>d(on)</sub>		-	120	-	
Rise time	t <sub>r</sub>		-	60	-	ns
Turn-off delay time	t <sub>d(off)</sub>	$V_{CC} = 600 \text{ V}, I_C = 400 \text{ A}, R_g = 4 \Omega,$ $V_{GE} = \pm 15 \text{ V}, T_J = 125 \text{ °C}$	-	490	-	
Fall time	t <sub>f</sub>		-	75	-	
Turn-on switching loss	E <sub>on</sub>		-	35	-	mJ
Turn-off switching loss	E <sub>off</sub>		-	46	-	1110
Input capacitance	C <sub>ies</sub>		-	30	-	
Output capacitance	C <sub>oes</sub>	$V_{GE} = 0 \text{ V}, V_{CE} = 25 \text{ V}, f = 1.0 \text{ MHz}$	-	4	-	nF
Reverse transfer capacitance	C <sub>res</sub>	1	-	3	-	
SC data	I <sub>SC</sub>	$t_{sc} \leq 10 \; \mu s, \; V_{GE} = 15 \; V, \; T_J = 125 \; ^{\circ}C, \\ V_{CC} = 900 \; V, \; V_{CEM} \leq 1200 \; V$	-	1900	-	Α
Stray inductance	L <sub>CE</sub>		-	-	20	nH
Module lead resistance, terminal to chip	R <sub>CC'+EE'</sub>	T <sub>C</sub> = 25 °C	-	0.18	-	mΩ

<b>DIODE ELECTRICAL SPECIFICATIONS</b> (T <sub>C</sub> = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDIT	TEST CONDITIONS		TYP.	MAX.	UNITS
Diode forward voltage	V <sub>F</sub>	I <sub>F</sub> = 400 A	T <sub>J</sub> = 25 °C	-	2.1	2.2	V
Diode forward voltage			T <sub>J</sub> = 125 °C	-	2.2	2.3	
Diada rayaraa raaayany aharga	Q <sub>rr</sub>	r	T <sub>J</sub> = 25 °C	-	40	-	
Diode reverse recovery charge			T <sub>J</sub> = 125 °C	-	48		μC
Diada mask variance vacariani, accument	I <sub>rr</sub>	$I_{rr} = \begin{array}{c} I_F = 400 \text{ A, } V_R = 600 \text{ V,} \\ dI/dt = -4000 \text{ A/}\mu\text{s,} \\ V_{GE} = -15 \text{ V} \end{array}$	T <sub>J</sub> = 25 °C	-	320	-	^
Diode peak reverse recovery current			T <sub>J</sub> = 125 °C	-	400		Α
Diada wayawa waaayaw anaway	E <sub>rec</sub>		T <sub>J</sub> = 25 °C	-	12	-	ml
Diode reverse recovery energy			T <sub>J</sub> = 125 °C	-	20	=	mJ

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature ran	ige T <sub>J</sub>		-40	-	150	°C
Storage temperature range	T <sub>Stg</sub>		-40	-	125	
Junction to case IGE	Т		-	-	0.05	
per module Dioc	le R <sub>thJC</sub>		-	-	0.09	K/W
Case to sink	R <sub>thCS</sub>	Conductive grease applied	-	0.035	-	
Mounting toward		Power terminal screw: M6	2.5 to 5.0		Nm	
Mounting torque		Mounting screw: M6		3.0 to 6.0	)	INITI
Weight				310		g

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## Vishay Semiconductors

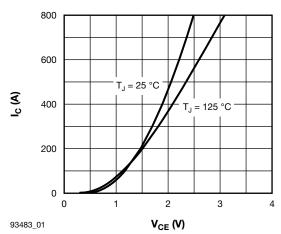


Fig. 1 - Typical Output Characteristics  $V_{GE} = 15 \text{ V}$ 

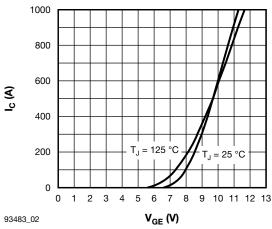


Fig. 2 - Typical Transfer Characteristics  $V_{CE} = 20 \text{ V}$ 

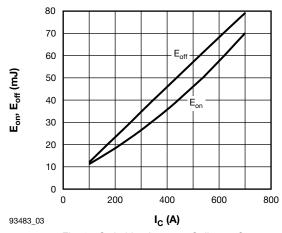


Fig. 3 - Switching Loss vs. Collector Current V<sub>CC</sub> = 600 V, R<sub>g</sub> = 4  $\Omega$ , V<sub>GE</sub> =  $\pm$  15 V, T<sub>J</sub> = 125 °C

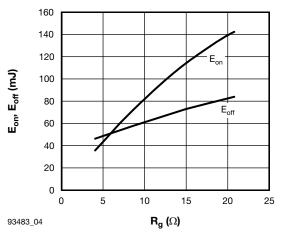


Fig. 4 - Switching Loss vs. Gate Resistor  $V_{CC}$  = 600 V,  $I_{C}$  = 400 A,  $V_{GE}$  =  $\pm$  15 V,  $T_{J}$  = 125  $^{\circ}C$ 

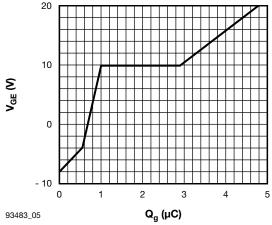


Fig. 5 - Gate Charge Characteristics  $V_{CC} = 600 \text{ V}, I_C = 400 \text{ A}, T_J = 25 ^{\circ}\text{C}$ 

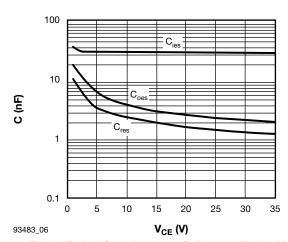


Fig. 6 - Typical Capacitance vs. Collector to Emitter Voltage



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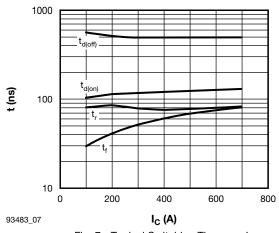


Fig. 7 - Typical Switching Times vs. I<sub>C</sub> V<sub>CC</sub> = 600 V, R<sub>g</sub> = 4  $\Omega$ , V<sub>GE</sub> =  $\pm$  15 V, T<sub>J</sub> = 125 °C

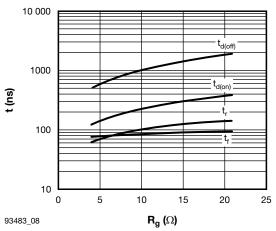


Fig. 8 - Typical Switching Times vs. Gate Resistance  $V_{CC}$  = 600 V,  $I_{C}$  = 400 A,  $V_{GE}$  = ± 15 V,  $T_{J}$  = 125 °C

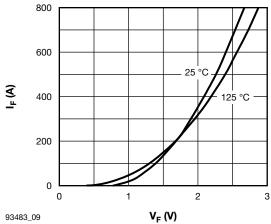


Fig. 9 - Typical Forward Characteristics (Diode)

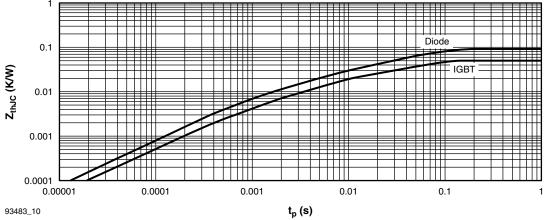
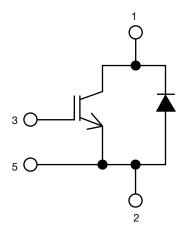


Fig. 10 - Transient Thermal Impedance



#### **CIRCUIT CONFIGURATION**

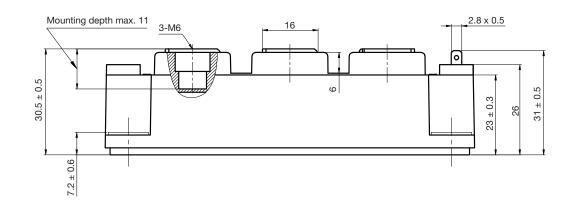


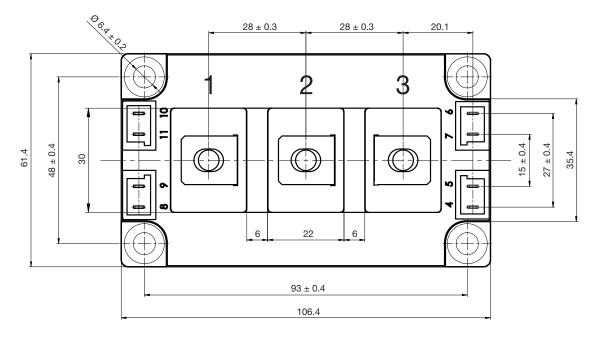
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95526			



## **Double INT-A-PAK**

#### **DIMENSIONS** in millimeters (inches)







## **Legal Disclaimer Notice**

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